



100V N-Channel Enhancement Mode MOSFET

Voltage

100 V

Current

13A

Features

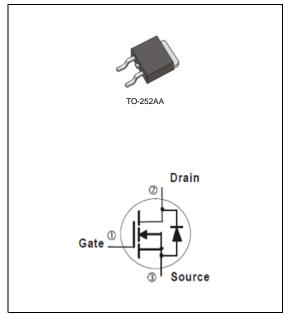
- RDS(ON), VGS@10V, ID@6.5A<115mΩ
- RDS(ON) , VGS@4.5V, ID@4A<120mΩ
- Advanced Trench Process Technology
- High density cell design for ultra low on-resistance
- Lead free in compliance with EU RoHS 2011/65/EU directive
- Green molding compound as per IEC61249 Std.. (Halogen Free)

Mechanical Data

• Case: TO-252AA Package

• Terminals: Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0104 ounces, 0.297 grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V_{DS}	100	V	
Gate-Source Voltage		V_{GS}	<u>+</u> 20	V	
Continuous Drain Current	T _C =25°C	l _D	13	А	
	T _C =100°C		8		
Pulsed Drain Current (Note 1)	T _C =25°C	I _{DM}	52	ı	
Power Dissipation	T _C =25°C	Po	41	W	
	T _C =100°C		16		
Continuous Drain Current	T _A =25°C	I _D	2.9	А	
	T _A =70°C		2.3	А	
Power Dissipation	T _A =25°C		2.0	W	
	T _A =70°C	Pb	1.3		
Single Pulse Avalanche Energy (Note 6)		E _{AS}	6.1	mJ	
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~150	°C	
Typical Thermal Resistance (Note 4,5	Junction to Case	$R_{ heta JC}$	3.05	°C/W	
	Junction to Ambient	$R_{\theta JA}$	62.5		

Limited only By Maximum Junction Temperature





Electrical Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	V _{GS} =0V,I _D =250uA	100	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250uA$	1.0	1.76	2.5	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V,I _D =6.5A	-	92	115	mΩ
		V _{GS} =4.5V,I _D =4A	-	95	120	
Zero Gate Voltage Drain Current	I_{DSS}	V _{DS} =100V,V _{GS} =0V	-	-	1.0	uA
Gate-Source Leakage Current	I_{GSS}	V _{GS} = <u>+</u> 20V,V _{DS} =0V	1	-	<u>+</u> 100	nA
Dynamic (Note 7)						
Total Gate Charge	Q_{g}	V _{DS} =50V, I _D =2A, V _{GS} =10V (Note 1,2)	-	20	-	nC
Gate-Source Charge	Q_gs		-	3.2	-	
Gate-Drain Charge	Q_gd		-	3.6	-	
Input Capacitance	Ciss	V _{DS} =25V, V _{GS} =0V, f=1.0MHZ	-	1413	-	pF
Output Capacitance	Coss		-	60	-	
Reverse Transfer Capacitance	Crss		-	34	-	
Turn-On Delay Time	td _(on)	\/ 50\/ L 4A	-	18	-	
Turn-On Rise Time	t _r	V_{DD} =50V, I_{D} =1A, V_{GS} =10V, R_{G} =3.3 Ω (Note 1,2)	-	4.3	-	ns
Turn-Off Delay Time	td _(off)		-	41	-	
Turn-Off Fall Time	t _f	K _G =3.312	1	4.2	-	
Drain-Source Diode						
Maximum Continuous Drain-Source			-	-	13	А
Diode Forward Current	I _S					
Diode Forward Voltage	V_{SD}	I _S =1A,V _{GS} =0V	-	0.73	1	V

NOTES:

- 1. Pulse width<a>300us, Duty cycle<a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial TJ =25°C.
- 4. The maximum current rating is package limited.
- 5. R_{OJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. The test condition is L=0.1mH, I_{AS} =11A, V_{DD} =25V, V_{GS} =10V
- 7. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

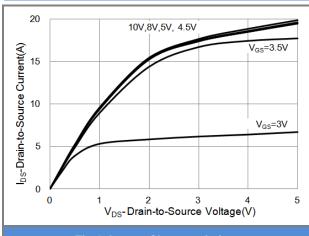
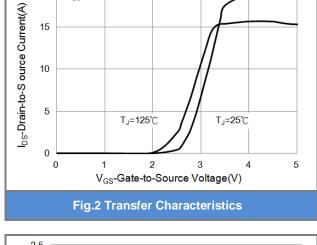


Fig.1 Output Characteristics



20

V_{DS}=5V

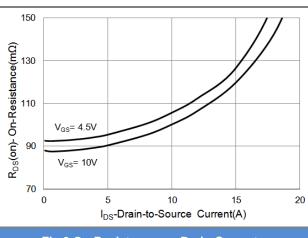


Fig.3 On-Resistance vs. Drain Current

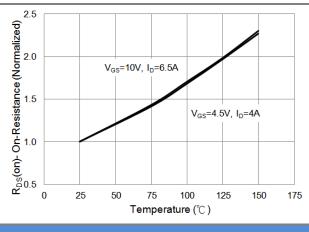
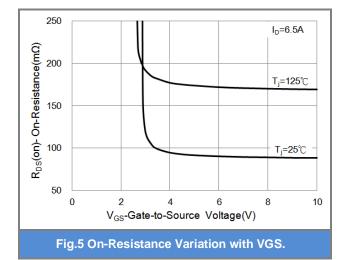


Fig.4 On-Resistance vs. Junction temperature



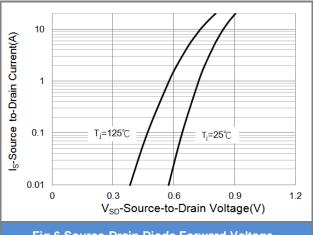


Fig.6 Source-Drain Diode Forward Voltage





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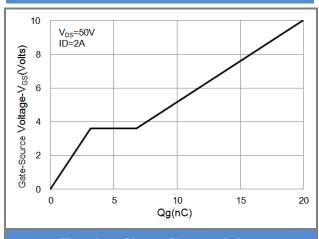


Fig.7 Gate-Charge Characteristics

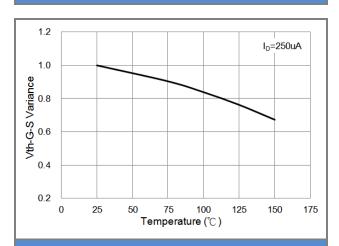


Fig.9 Threshold Voltage Variation with Temperature

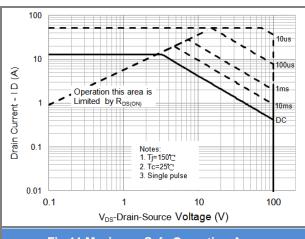


Fig.11 Maximum Safe Operating Area

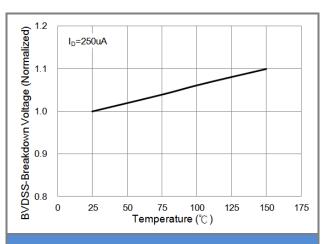


Fig.8 Breakdown Voltage Variation vs. Temperature

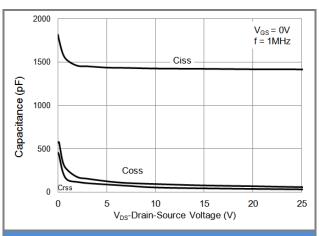


Fig.10 Capacitance vs. Drain-Source Voltage





TYPICAL CHARACTERISTIC CURVES

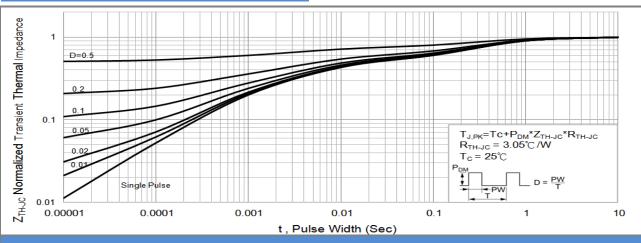
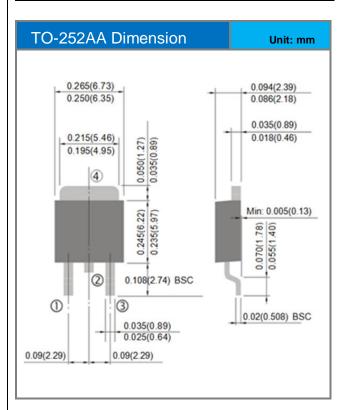


Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width





Packaging Information



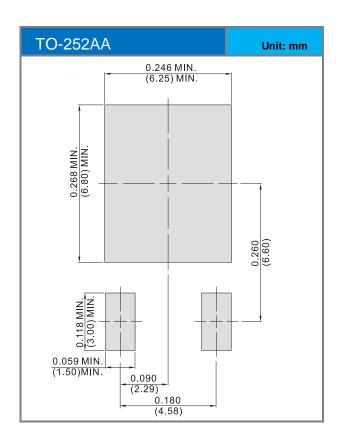




PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJD13N10A_L2_00001	TO-252AA	3,000pcs / 13" reel	D13N10A	Halogen free

MOUNTING PAD LAYOUT







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